SemTron Microtech Corporation

STN8205A

20V N-Channel Enhancement Mode MOSFET

N-Channel Enhancement Mode MOSFET

DESCRIPTION

The STN8205A is the Dual N-Channel logic enhancement mode power field effect transistor which is produced using high cell density. advanced trench technology to provide excellent $R_{DS(ON)}$.

This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application , and low in-line power loss are needed in a very small outline surface mount package.

STN8205AS-TRG ROHS Compliant This is Halogen Free

FEATURE

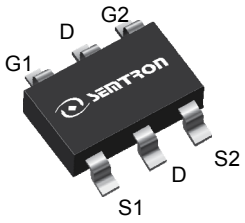
- ***30V/6.0A, $R_{DS(ON)}$ =21mΩ(typ.)@V_{GS} =4.5V***
- ***30V/5.2A, $R_{DS(ON)}$ =25mΩ(typ.)@V_{GS} =2.5V***
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and Maximum DC current capability

APPLICATIONS

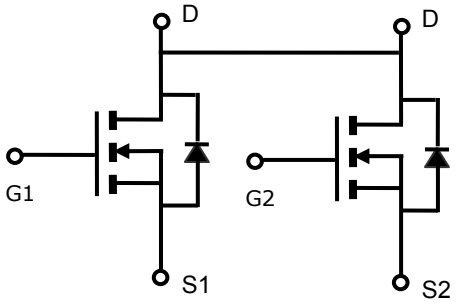
- Power Management in Note book
- Portable Equipment
- Battery Powered System

Green Product

PIN CONFIGURATION



SOT-23-6L
Top View



PART NUMBER INFORMATION

ST N 8205A S - TR G a b c d e f	**a : Company name.** **b : Channel type.** **c : Product Serial number.** **d : Package Code** **e : Handling Code** **f : Lead Plating Code** G : Lead-free product. ***This product is Halogen Free***

■ORDERING INFORMATION

Part Number	Package Code	Handling Code	Shipping
STN8205AS-TRG	S6 : SOT-23-6L	TR : Tape&Reel	3K/Reel

※ Year Code : 0 ~ 9, 2010 : 0
※ Week Code : A(1~2) ~ Z(53~54)
※ SOT-23L : Only available in tape and reel packaging.

■ABSOLUTE MAXIMUM RATINGS (T_A = 25℃ Unless otherwise noted)

Symbol	Parameter		Typical	Unit
V_{DSS}	Drain-Source Voltage		20	V
V_{GSS}	Gate-Source Voltage		±12	V
I_D	Continuous Drain Current (T_C=25°C) [A]	V_{GS}=10V	6.0	A
	Continuous Drain Current (T_C=70°C) [A]		5.0	A
I_{DM}	Pulsed Drain Current [B]		20	A
P_D	Power Dissipation	T_A=25°C T_A=70°C	1.5 0.9	W
T_J	Operation Junction Temperature		-55 to150	°C
T_{STG}	Storage Temperature Range		-55 to150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■THERMAL DATA

Symbol	Parameter		Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient [A]	Steady-State	-	80	°C/W
$R_{\theta JL}$	Thermal Resistance Junction to Lead [A]	Steady-State	-	62.5	°C/W

■ELECTRICAL CHARACTERISTICS(T_J = 25℃ Unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=250μA	20			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	0.5		1.0	V
I_{GSS}	Gate Leakage Current	V_{DS}=0V,V_{GS}=±12V			±100	nA
I_{DSS}	Zero Gate Voltage, Drain-Source Leakage Current	V_{DS}=16V,V_{GS}=0V T_J=25°C			1	μA
		V_{DS}=16V,V_{GS}=0V T_J=55°C			5	
$R_{DS(ON)}$	Drain-source On-Resistance[B]	V_{GS}=4.5V,I_D=6.0A V_{GS}=2.5V,I_D=5.2A		21 25	25 32	mΩ
G_{fs}	Forward Transconductance	V_{DS}=15V,I_D=3.6A		10		S
Source-Drain Doide						
V_{SD}	Diode Forward Voltage	I_S=1.0A,V_{GS}=0V		0.7	1.0	V
I_S	Continuous Source Current[AD]				10	A
Dynamic Parameters						
Q_g (4.5V)	Total Gate Charge	V_{DS}=10V V_{GS}=4.5V I_D≡6.0A		21	29	nC
Q_{gs}	Gate-Source Charge			1.3		
Q_{gd}	Gate-Drain Charge			3.3		
C_{iss}	Input Capacitance	V_{DS}=10V V_{GS}=0V f=1MHz		580		pF
C_{oss}	Output Capacitance			138		
C_{rss}	Reverse Transfer Capacitance			120		
$t_{d(on)}$	Turn-On Time	V_{DD}=10V I_D=6A V_{GEN}=4.5V R_G=3.3Ω		3.5	7	nS
t_r				13.5	24	
$t_{d(off)}$	Turn-Off Time			32	58	
t_f				6.6	13	

Note:

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

B. The data tested by pulsed , pulse width ≦ 300uS , duty cycle ≦ 2%

C. The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.1mH.

D. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

The products and product specifications contained herein are subject to change without notice to improve performance characteristics. Consult us, or our representatives before use, to confirm that the information in this datasheet is up to date

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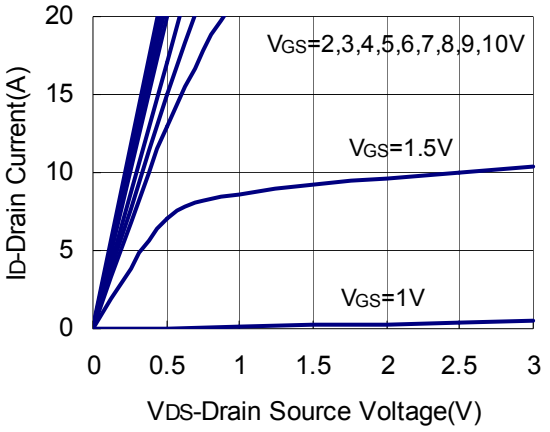
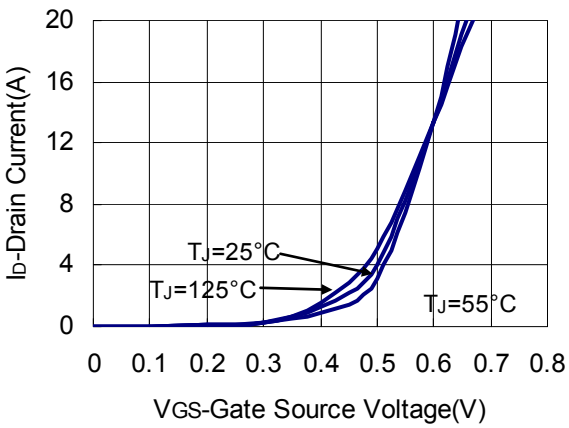
TYPICAL CHARACTERISTICS (25℃ Unless Note)

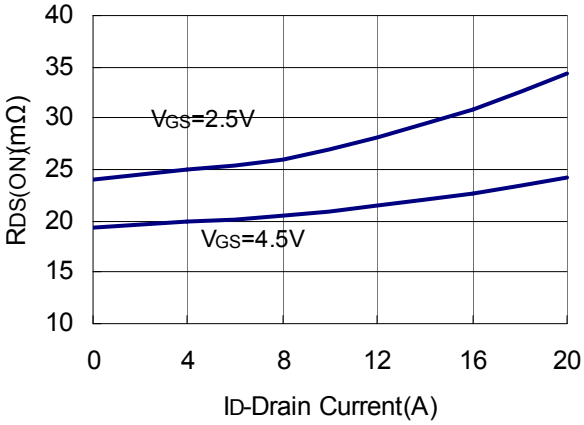
Output Characteristics



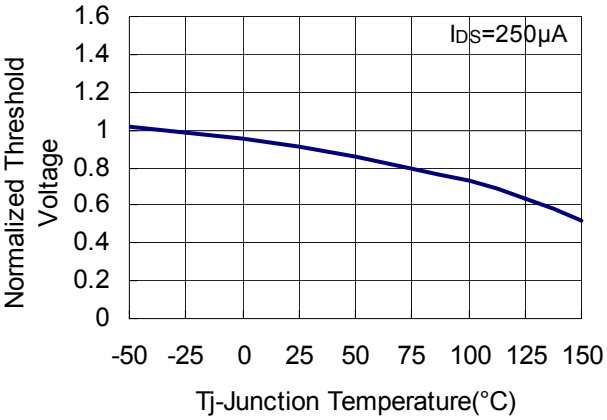
Drain-Source On Resistance



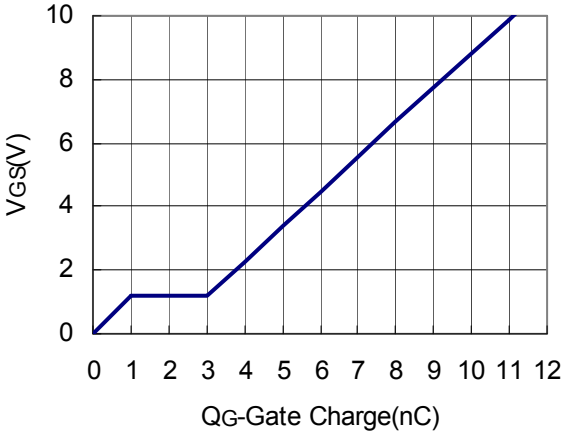
Transfer Characteristics



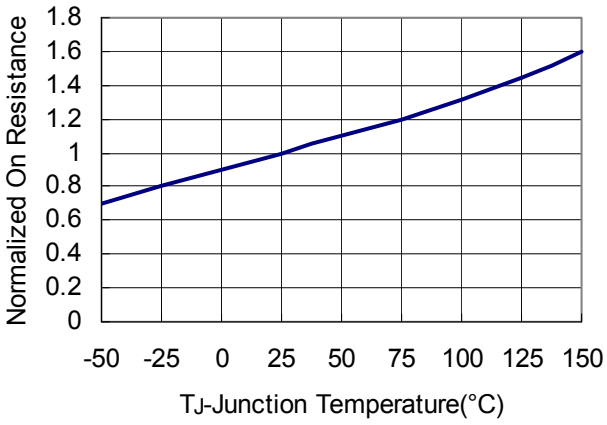
Gate Threshold Voltage



Gate Charge

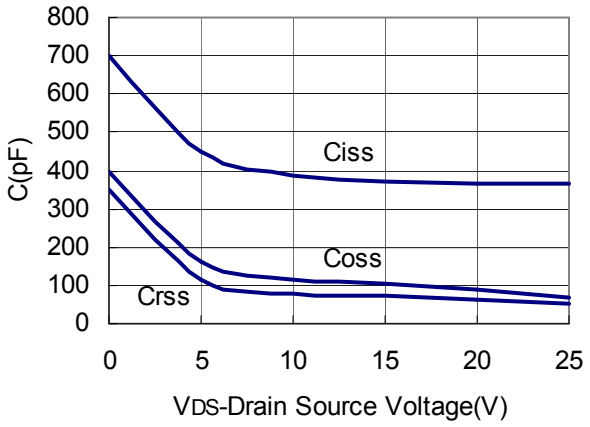


Drain Source On Resistance

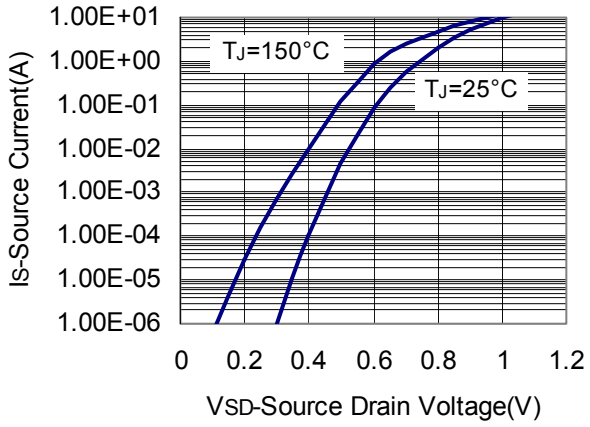


TYPICAL CHARACTERISTICS (25℃ Unless Note)

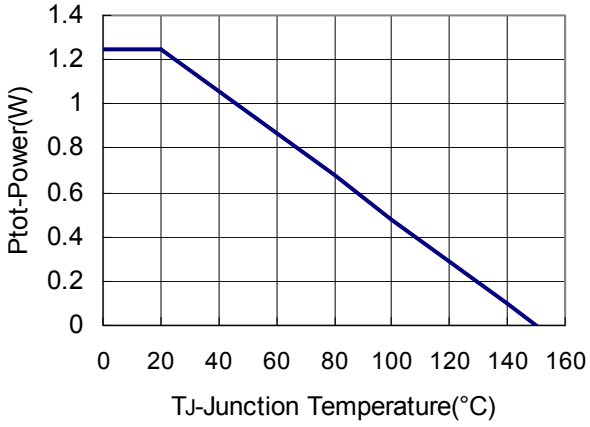
Capacitance



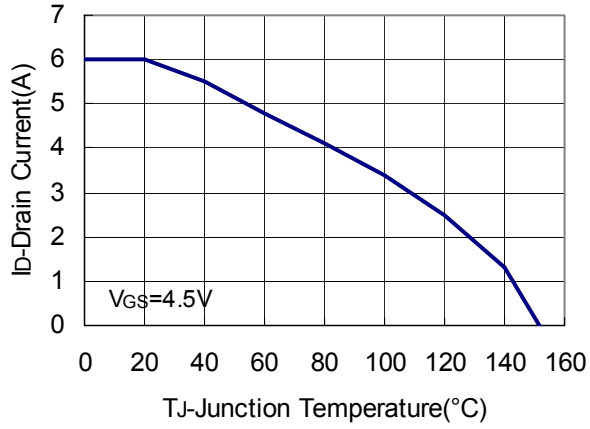
Source Drain Diode Forward



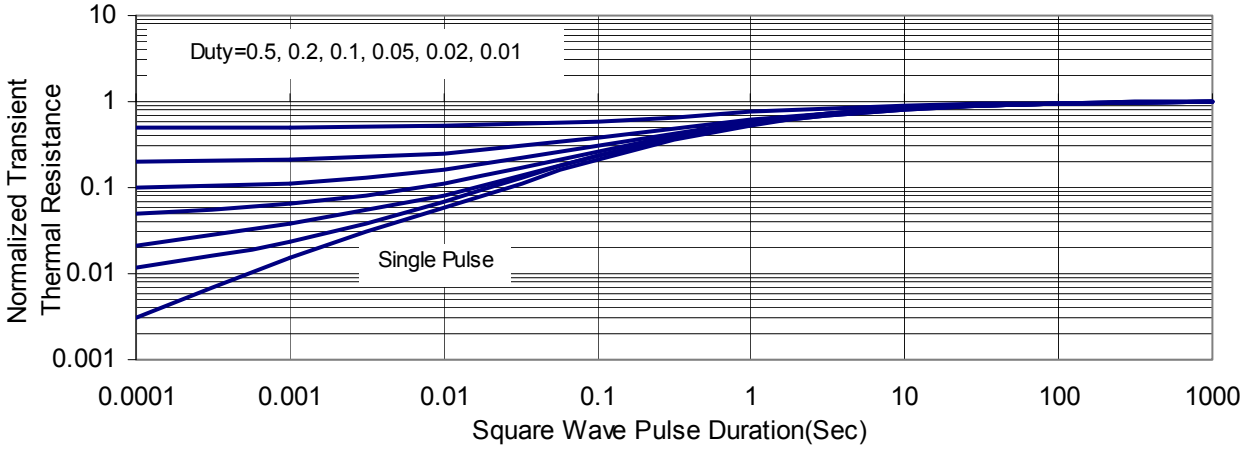
Power Dissipation



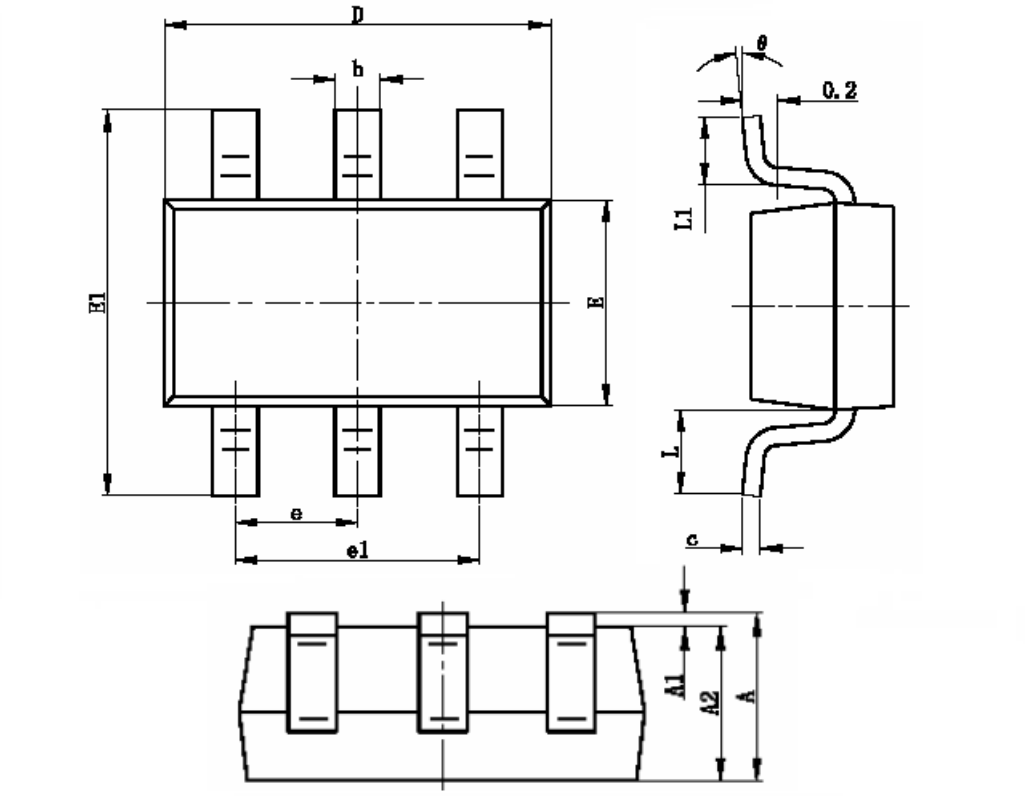
Drain Current



Thermal Transient Impedance



SOT-23-6L PACKAGE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.400	0.012	0.016
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.700REF		0.028REF	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°